

International IR Rectifier

SERIES IRK.136, .142, .162

**THYRISTOR/DIODE and
THYRISTOR/THYRISTOR**

NEW INT-A-pak Power Modules

Features

- High Voltage
- Electrically Isolated by DBC Ceramic (Al_2O_3)
- 3500 V_{RMS} Isolating Voltage
- Industrial Standard Package
- High Surge Capability
- Glass Passivated Chips
- Modules uses High Voltage Power thyristor/diodes in three Basic Configurations
- Simple Mounting
- UL E78996 approved 

135 A
140 A
160 A

Applications

- DC Motor Control and Drives
- Battery Charges
- Welders
- Power Converters
- Lighting Control
- Heat and Temperature Control

Major Ratings and Characteristics

Parameters	IRK.136..	IRK.142..	IRK.162..	Units	
$I_{T(AV)}$	135	140	160	A	
@ T_C	85	85	85	°C	
$I_{T(RMS)}$	300	310	355	A	
I_{TSM}	@ 50Hz	3200	4500	4870	A
	@ 60Hz	3360	4712	5100	A
I^2t	@ 50Hz	51.5	102	119	KA ² s
	@ 60Hz	47	92.5	108	KA ² s
$I^2\sqrt{t}$	515.5	1013	1190	KA ² √s	
V_{RRM}	400 to 1600			V	
T_J range	-40 to 125			°C	

CASE STYLE NEW INT-A-PAK



Electrical Specifications

Voltage Ratings

Type number	Voltage Code	V_{RRM}/V_{DRM} , Maximum repetitive peak reverse voltage V	V_{RSM}/V_{DSM} , Maximum non-repetitive peak reverse voltage V	I_{RRM}/I_{DRM} @ 125°C mA
IRK.136	04	400	500	50
IRK.142	08	800	900	
IRK.162	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

Forward Conduction

Parameter	IRK.136	IRK.142	IRK.162	Units	Conditions	
$I_{T(AV)}$ Max. average on-state current @ Case temperature	135	140	160	A	180° conduction, half sine wave	
	85	85	85	°C		
$I_{T(RMS)}$ Max. RMS on-state current	300	310	355	A	as AC switch	
I_{TSM} Maximum peak, one-cycle on-state, non-repetitive surge current	3200	4500	4870	A	t = 10ms No voltage	Sine half wave, Initial $T_J = T_{J \text{ max.}}$
	3360	4712	5100		t = 8.3ms reappplied	
	2700	3785	4100		t = 10ms 100% V_{RRM}	
	2800	3963	4300		t = 8.3ms reappplied	
I^2t Maximum I^2t for fusing	51.5	102	119	KA ² s	t = 10ms No voltage	
	47	92.5	108		t = 8.3ms reappplied	
	36.5	71.6	84		t = 10ms 100% V_{RRM}	
	33.3	65.4	76.7		t = 8.3ms reappplied	
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	515.5	1013	1190	KA ² √s	t = 0.1 to 10ms, no voltage reappplied	
$V_{T(TO)1}$ Low level value of threshold voltage	0.86	0.83	0.8	V	(16.7% × π × $I_{T(AV)}$) < I < π × $I_{T(AV)}$, @ $T_{J \text{ max.}}$	
$V_{T(TO)2}$ High level value of threshold voltage	1.05	1	0.98		(I > π × $I_{T(AV)}$), @ $T_{J \text{ max.}}$	
$r_{\theta 1}$ Low level value on-state slope resistance	2.02	1.78	1.67	mΩ	(16.7% × π × $I_{T(AV)}$) < I < π × $I_{T(AV)}$, @ $T_{J \text{ max.}}$	
$r_{\theta 2}$ High level value on-state slope resistance	1.65	1.43	1.38		(I > π × $I_{T(AV)}$), @ $T_{J \text{ max.}}$	
V_{TM} Maximum forward voltage drop	1.57	1.55	1.54	V	$I_{TM} = \pi \times I_{T(AV)}$, $T_J = 25^\circ\text{C}$, 180° conduction	
I_H Maximum holding current	200			mA	Anode supply = 6V initial $I_r = 30A$, $T_J = 25^\circ\text{C}$	
I_L Maximum latching current	400			mA	Anode supply = 6V resistive load = 1Ω Gate pulse: 10V, 100μs, $T_J = 25^\circ\text{C}$	

Switching

t_{gd} Typical delay time	1	μs	$T_J = 25^\circ\text{C}$	Gate Current=1A $dI_g/dt=1A/\mu s$
t_{gr} Typical rise time	2		$T_J = 25^\circ\text{C}$	$V_d=0,67\% V_{DRM}$
t_q Typical turn-off time	50 - 200		$I_{TM} = 300A$; $-dI/dt = 15A/\mu s$; $T_J = T_{J \text{ max}}$ $V_r = 50V$; $dV/dt = 20V/\mu s$; Gate 0V, 100Ω	

Blocking

I_{RRM}	Maximum peak reverse and off-state leakage current	50	mA	$T_J = 125^\circ\text{C}$
I_{DRM}	Maximum peak reverse and off-state leakage current			
V_{INS}	RMS isolation voltage	3500	V	50Hz, circuit to base, all terminals shorted, $t = 1\text{s}$
dV/dt	critical rate of rise of off-state voltage	1000	V/ μs	$T_J = T_{J\text{max.}}$, exponential to 67% rated V_{DRM}

Triggering

Parameter	IRK.136	IRK.142	IRK.162	Units	Conditions	
P_{GM}	Max. peak gate power			12	W	$t_p \leq 5\text{ms}$, $T_J = T_{J\text{max.}}$
$P_{G(AV)}$	Max. average gate power			3	W	$f = 50\text{Hz}$, $T_J = T_{J\text{max.}}$
I_{GM}	Max. peak gate current			3	A	$t_p \leq 5\text{ms}$, $T_J = T_{J\text{max.}}$
$-V_{GT}$	Max. peak negative gate voltage			10	V	
V_{GT}	Max. required DC gate voltage to trigger			4	V	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = T_{J\text{max.}}$ Anode supply = 6V, resistive load; $R_a = 1\Omega$
				2.5		
				1.7		
I_{GT}	Max. required DC gate current to trigger			270	mA	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = T_{J\text{max.}}$ Anode supply = 6V, resistive load; $R_a = 1\Omega$
				150		
				80		
V_{GD}	Max. gate voltage that will not trigger			0.3	V	@ $T_J = T_{J\text{max.}}$, rated V_{DRM} applied
I_{GD}	Max. gate current that will not trigger			10	mA	
di/dt	Max. rate of rise of turned-on current			300	A/ μs	@ $T_J = T_{J\text{max.}}$, $I_{TM} = 400\text{A}$ rated V_{DRM} applied

Thermal and Mechanical Specifications

Parameter	IRK.136	IRK.142	IRK.162	Units	Conditions	
T_J	Max. junction operating temperature range			-40 to 125	$^\circ\text{C}$	
T_{stg}	Max. storage temperature range			-40 to 150	$^\circ\text{C}$	
R_{thJC}	0.18	0.18	0.16	K/W	DC operation, per junction	
R_{thCS}	Max. thermal resistance, case to heatsink			0.05	K/W	Mounting surface smooth, flat and greased Per module
T	Mounting torque $\pm 10\%$	IAP to heatsink		4 to 6	Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads.
		busbar to IAP		4 to 6		
wt	Approximate weight			200 (7.1)	g(oz)	
	Case Style			New Int-A-Pak		

ΔR Conduction (per Junction)

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Devices	Sinusoidal conduction @ $T_J\text{max.}$					Rectangular conduction @ $T_J\text{max.}$					Units
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
IRK.136	0.007	0.01	0.013	0.0155	0.017	0.009	0.012	0.014	0.015	0.017	K/W
IRK.142	0.0019	0.0019	0.0020	0.0020	0.0021	0.0018	0.0022	0.0023	0.0023	0.0020	
IRK.162	0.0030	0.0031	0.0032	0.0033	0.0034	0.0029	0.0036	0.0039	0.0041	0.0040	

IRK.136, .142, .162 Series

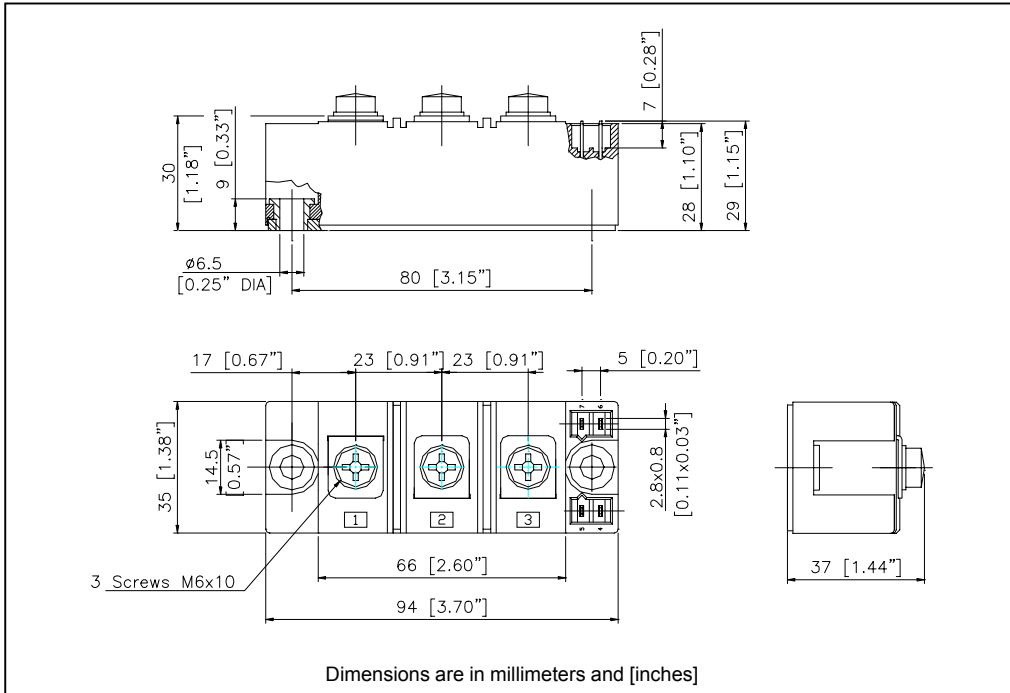
Bulletin I27117 rev. C 03/02

Ordering Information Table

Device Code				
1	2	3	4	
IRK	T	162	/	16
1	-			
2	-			
3	-			
4	-			

1 - Module Type
2 - Circuit Configuration
3 - Current Rating: $I_{T(AV)}$
4 - Voltage Code: Code x 100 = V_{RRM}

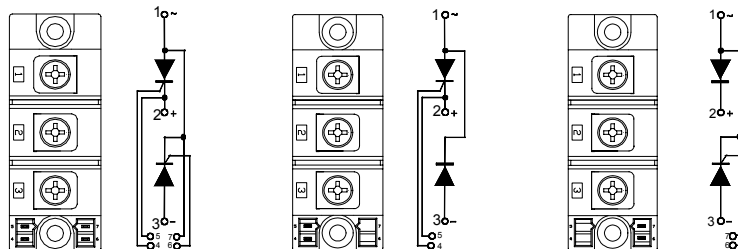
Outline Table



IRKT

IRKH

IRKL



NOTE: To order the Optional Hardware see Bulletin I27900



Fig. 1 - Current Ratings Characteristics

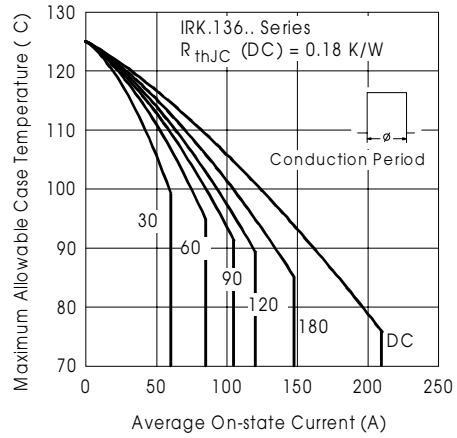


Fig. 2 - Current Ratings Characteristics



Fig. 3 - On-State Power Loss Characteristics

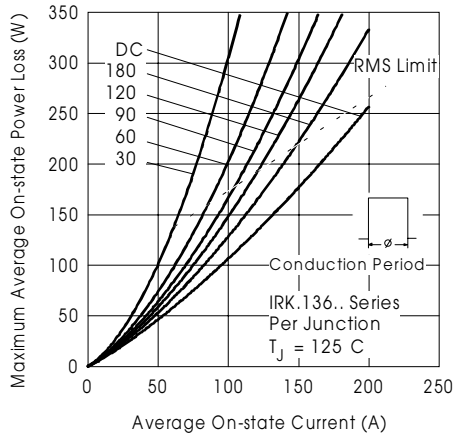


Fig. 4 - On-State Power Loss Characteristics

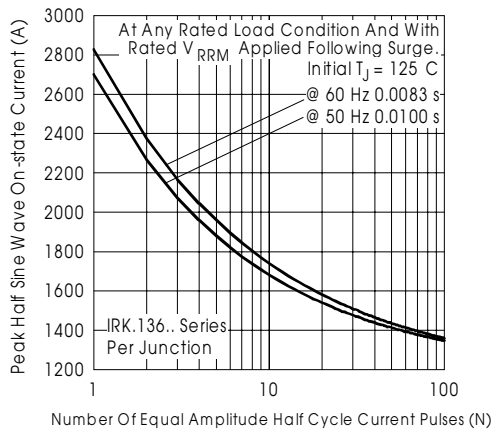


Fig. 5 - Maximum Non-Repetitive Surge Current

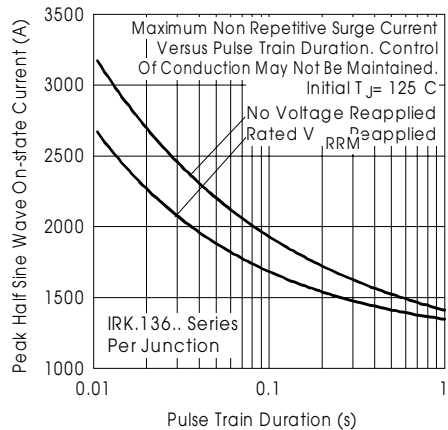


Fig. 6 - Maximum Non-Repetitive Surge Current

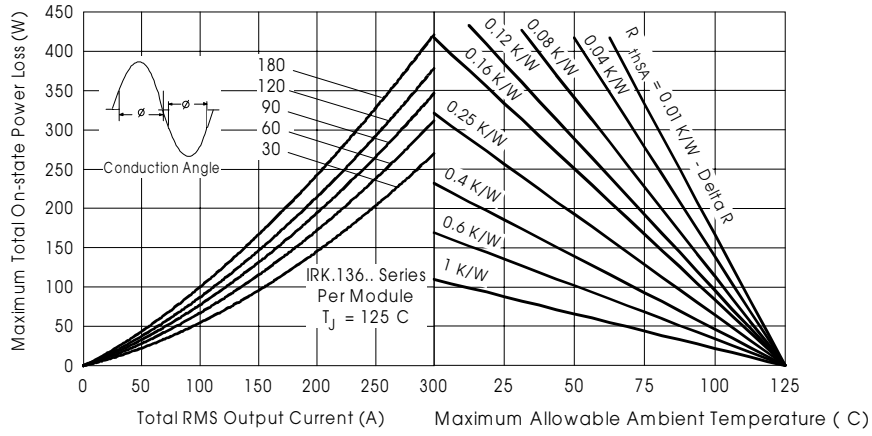


Fig.7 - On State Power Loss Characteristics

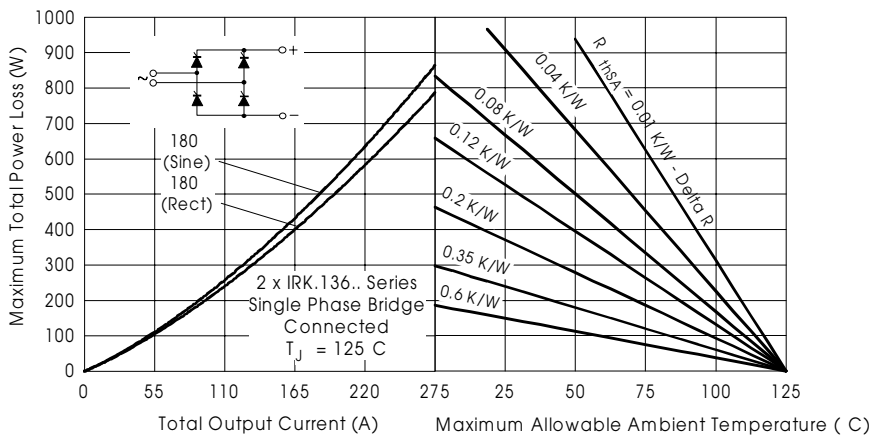


Fig.8 - On State Power Loss Characteristics

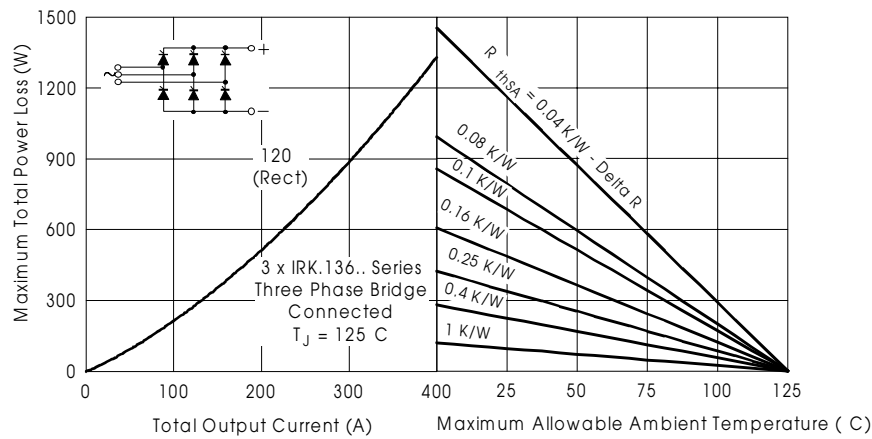


Fig.9 - On State Power Loss Characteristics

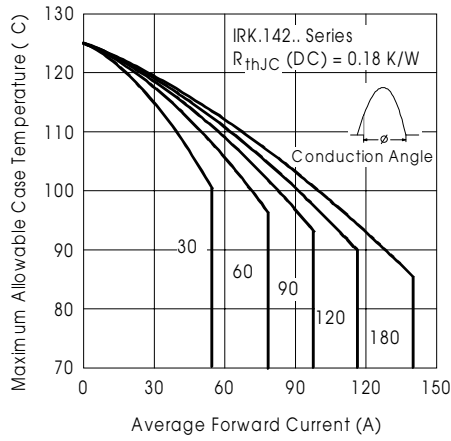


Fig. 10 - Current Ratings Characteristics

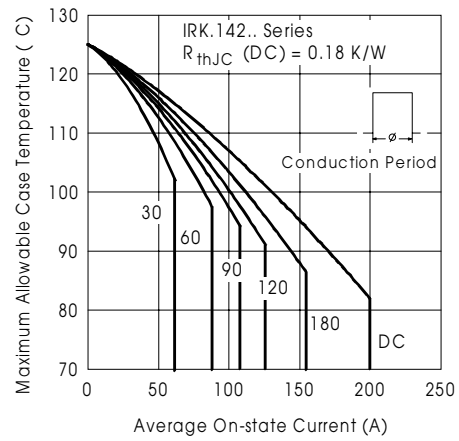


Fig. 11 - Current Ratings Characteristics

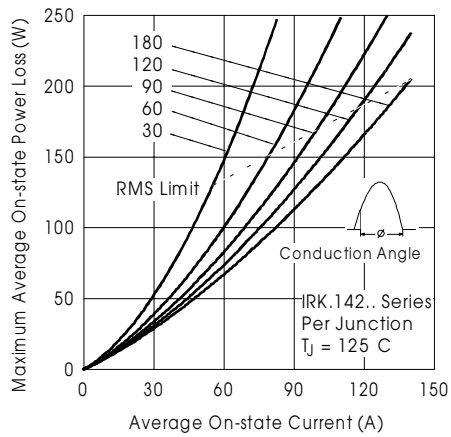


Fig. 12 - On-State Power Loss Characteristics

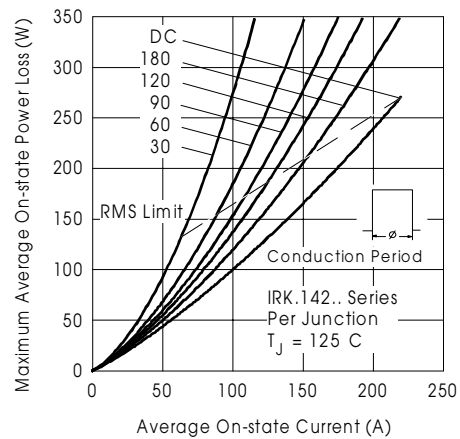


Fig. 13 - On-State Power Loss Characteristics

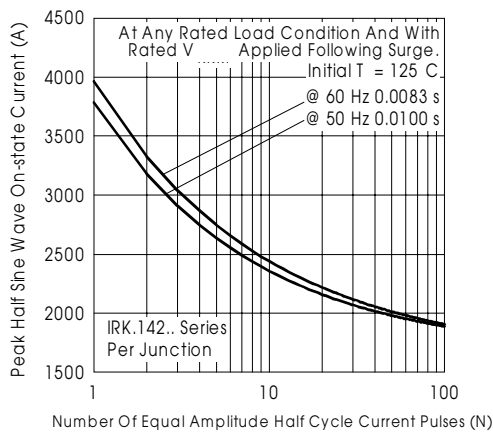


Fig. 14 - Maximum Non-Repetitive Surge Current

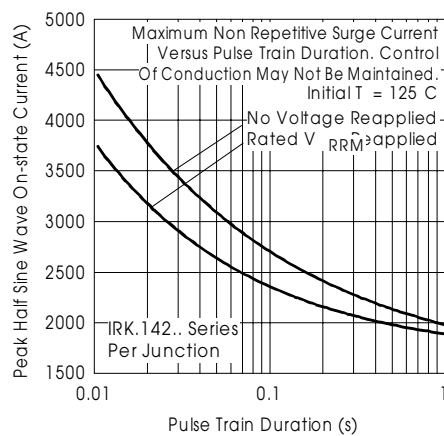


Fig. 15 - Maximum Non-Repetitive Surge Current

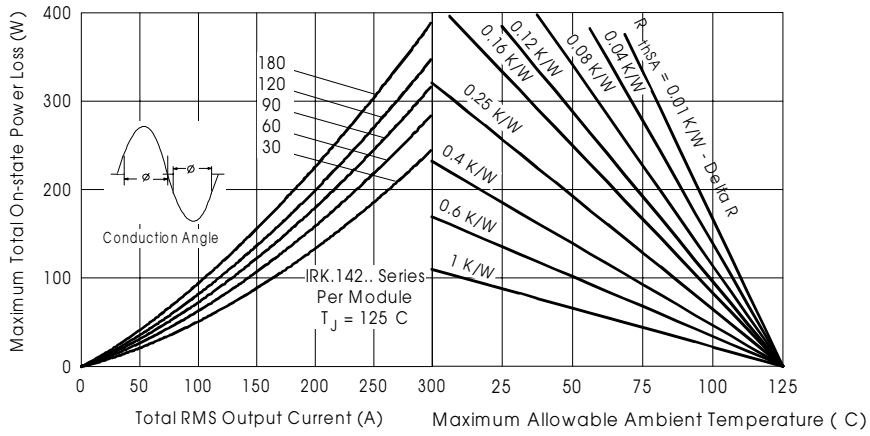


Fig.16 - On State Power Loss Characteristics

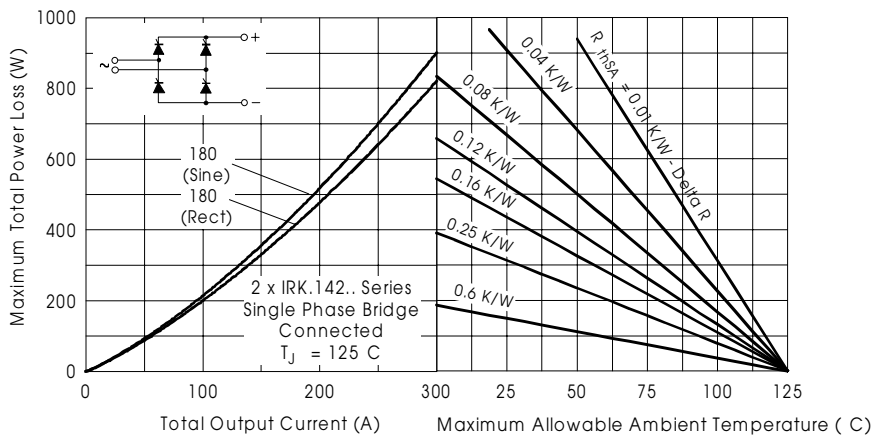


Fig.17 - On State Power Loss Characteristics

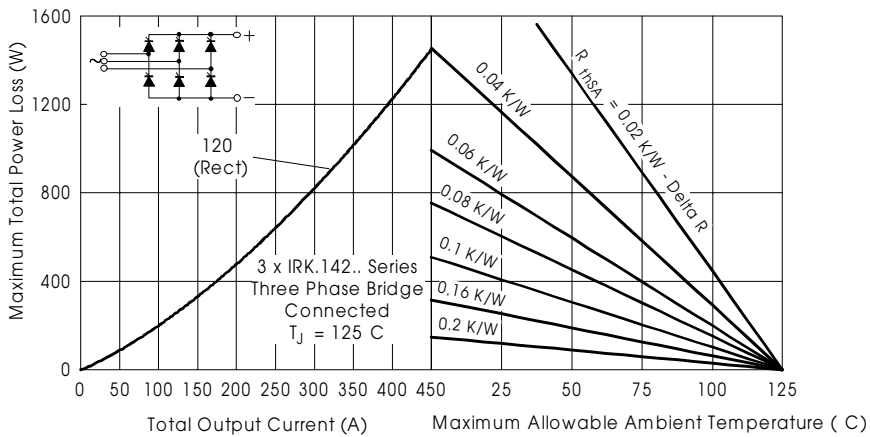


Fig.18 - On State Power Loss Characteristics



Fig. 19 - Current Ratings Characteristics



Fig. 20 - Current Ratings Characteristics



Fig. 21 - On-State Power Loss Characteristics



Fig. 22 - On-State Power Loss Characteristics

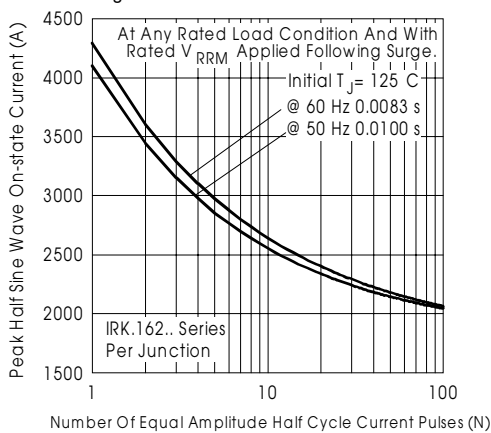


Fig. 23 - Maximum Non-Repetitive Surge Current

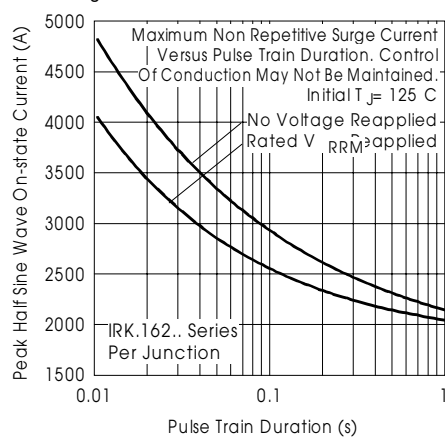


Fig. 24 - Maximum Non-Repetitive Surge Current

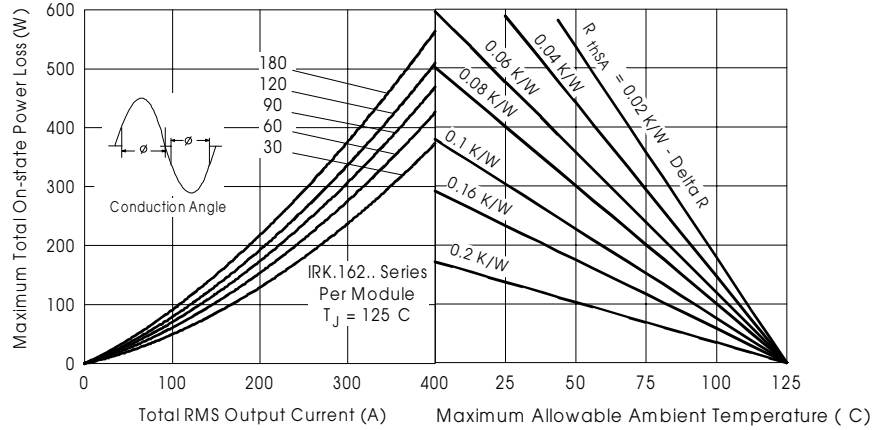


Fig.25 - On State Power Loss Characteristics

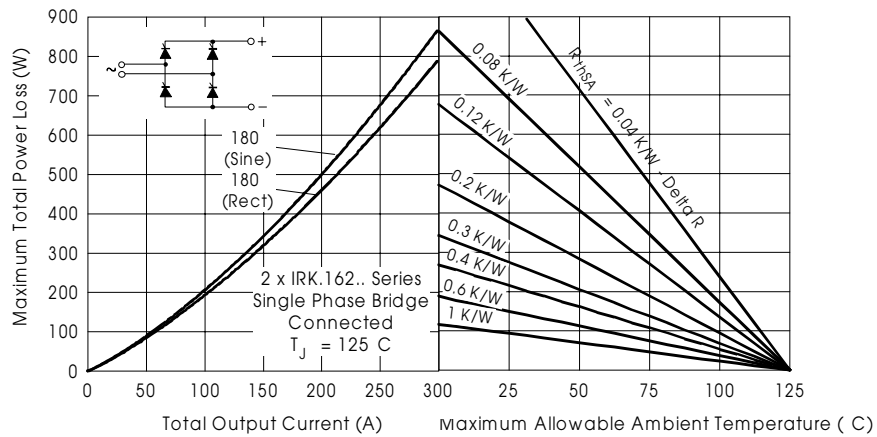


Fig.26 - On State Power Loss Characteristics

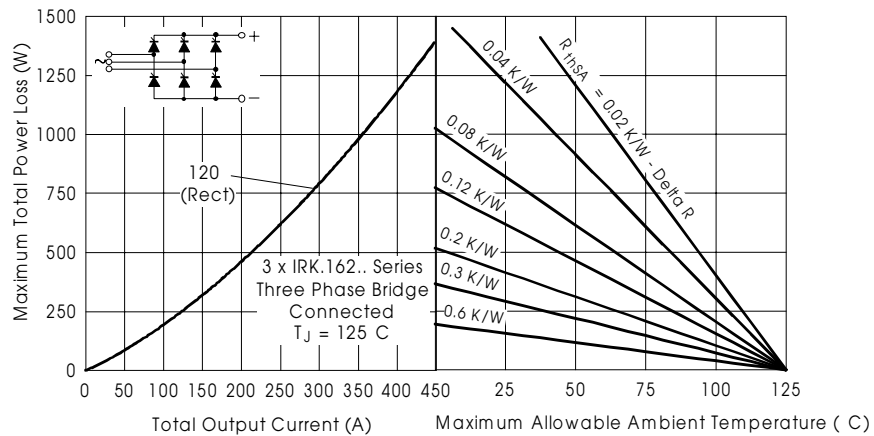


Fig.27 - On State Power Loss Characteristics



Fig.28 - On State Voltage Drop Characteristics



Fig.29 - On State Voltage Drop Characteristics

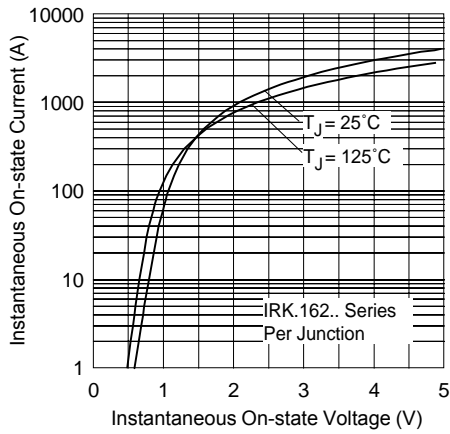


Fig.30 - On State Voltage Drop Characteristics

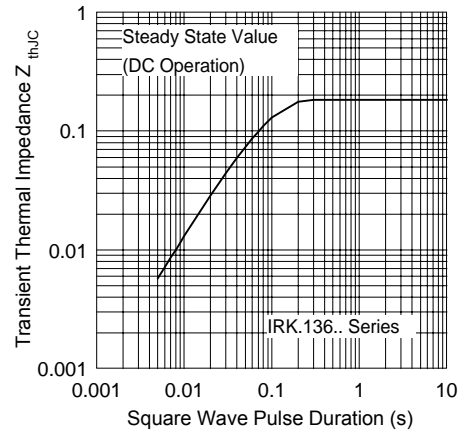


Fig.31 - Thermal Impedance ZthJC Characteristics



Fig.32 - Thermal Impedance ZthJC Characteristics

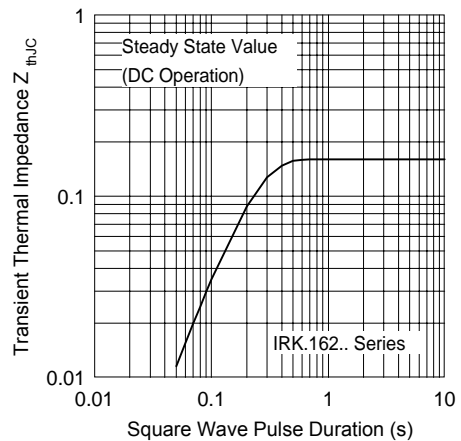


Fig.33 - Thermal Impedance ZthJC Characteristics

IRK.136, .142, .162 Series

Bulletin I27117 rev. C 03/02

International
IR Rectifier



Fig. 34 - Gate Characteristics

Data and specifications subject to change without notice.
 This product has been designed and qualified for Multiple Level.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7309
 Visit us at www.irf.com for sales contact information. 03/02